

Title (en)

SEMICONDUCTOR DEVICE AND METHOD

Title (de)

HALBLEITEREINRICHTUNG UND VERFAHREN

Title (fr)

DISPOSITIF A SEMI-CONDUCTEUR ET PROCEDE ASSOCIE

Publication

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Application

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Abstract (en)

[origin: WO2005020287A2] Methods and devices are disclosed for producing controllable light emission from a bipolar transistor. Also, a method is disclosed for increasing the speed of a bipolar transistor, including the following steps: providing a bipolar transistor having emitter, base, and collector regions; providing electrodes for coupling electrical signals with the emitter, base, and collector regions; and adapting the base region to enhance stimulated emission to the detriment of spontaneous emission, so as to reduce carrier recombination lifetime in the base region.

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IPC 8 full level

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